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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	157
Number of Gates	250000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/a3p250l-1fgg256

Introduction 213
Low Power Flash Device I/O Support 214
Pro I/Os—IGLOOe, ProASIC3EL, and ProASIC3E 215
I/O Architecture 220
I/O Standards 223
I/O Features 227
Simultaneously Switching Outputs (SSOs) and Printed Circuit Board Layout 241
I/O Software Support 242
User I/O Naming Convention 245
Board-Level Considerations 246
Conclusion 248
Related Documents 248
List of Changes 249

9 I/O Software Control in Low Power Flash Devices 251
Flash FPGAs I/O Support 252
Software-Controlled I/O Attributes 253
Implementing I/Os in Microsemi Software 254
Assigning Technologies and VREF to I/O Banks 264
Conclusion 269
Related Documents 269
List of Changes 270

10 DDR for Microsemi's Low Power Flash Devices 271
Introduction 271
Double Data Rate (DDR) Architecture 271
DDR Support in Flash-Based Devices 272
I/O Cell Architecture 273
Input Support for DDR 275
Output Support for DDR 275
Instantiating DDR Registers 276
Design Example 282
Conclusion 284
List of Changes 285

11 Programming Flash Devices 287
Introduction 287
Summary of Programming Support 287
Programming Support in Flash Devices 288
General Flash Programming Information 289
Important Programming Guidelines 295
Related Documents 297
List of Changes 298

12 Security in Low Power Flash Devices 301
Security in Programmable Logic 301
Security Support in Flash-Based Devices 302
Security Architecture 303
Security Features 304
Security in Action 308

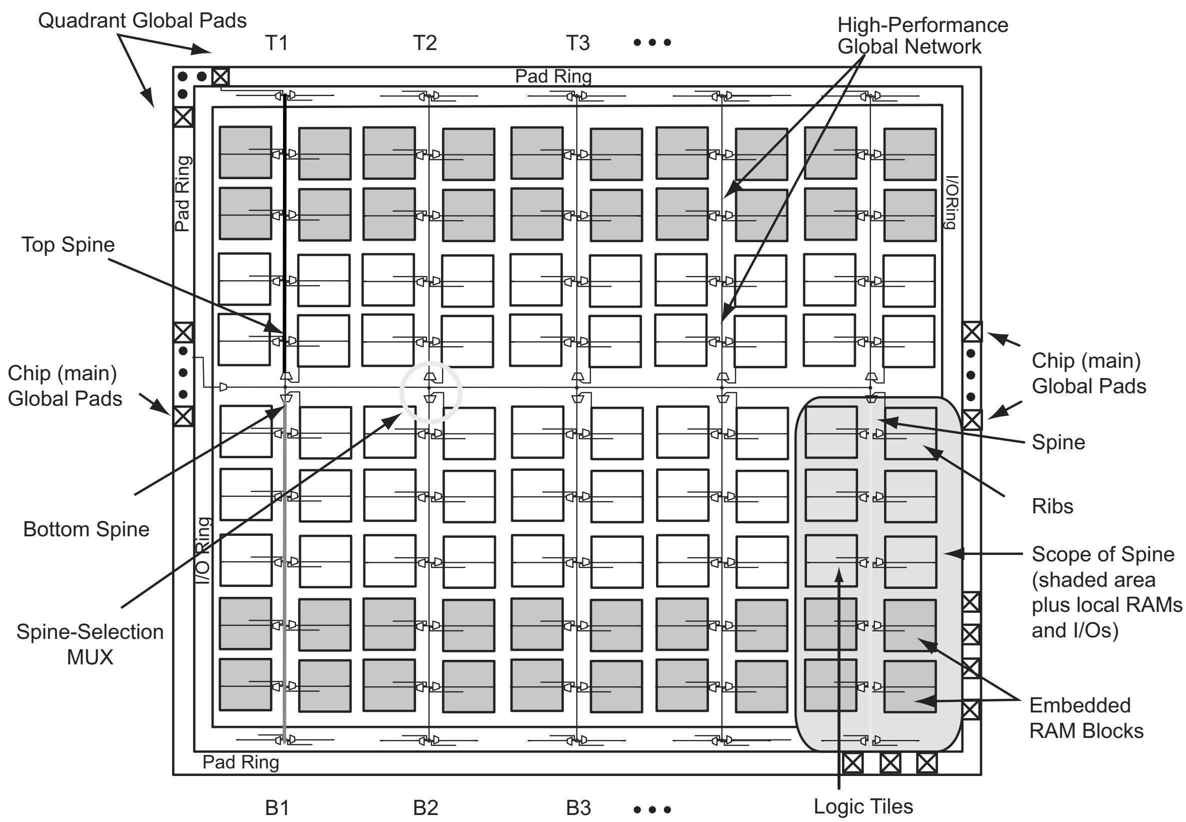
VersaNet Global Network Distribution

One of the architectural benefits of low power flash architecture is the set of powerful, low-delay VersaNet global networks that can access the VersaTiles, SRAM, and I/O tiles of the device. Each device offers a chip global network with six global lines (except for nano 10 k, 15 k, and 20 k gate devices) that are distributed from the center of the FPGA array. In addition, each device (except the 10 k through 30 k gate device) has four quadrant global networks, each consisting of three quadrant global net resources. These quadrant global networks can only drive a signal inside their own quadrant. Each VersaTile has access to nine global line resources—three quadrant and six chip-wide (main) global networks—and a total of 18 globals are available on the device (3 × 4 regional from each quadrant and 6 global).

Figure 3-1 shows an overview of the VersaNet global network and device architecture for devices 60 k and above. Figure 3-2 and Figure 3-3 on page 50 show simplified VersaNet global networks.

The VersaNet global networks are segmented and consist of spines, global ribs, and global multiplexers (MUXes), as shown in Figure 3-1. The global networks are driven from the global rib at the center of the die or quadrant global networks at the north or south side of the die. The global network uses the MUX trees to access the spine, and the spine uses the clock ribs to access the VersaTile. Access is available to the chip or quadrant global networks and the spines through the global MUXes. Access to the spine using the global MUXes is explained in the "Spine Architecture" section on page 57.

These VersaNet global networks offer fast, low-skew routing resources for high-fanout nets, including clock signals. In addition, these highly segmented global networks offer users the flexibility to create low-skew local clock networks using spines for up to 252 internal/external clocks or other high-fanout nets in low power flash devices. Optimal usage of these low-skew networks can result in significant improvement in design performance.



Note: Not applicable to 10 k through 30 k gate devices

***Figure 3-1* • Overview of VersaNet Global Network and Device Architecture**

***Table 3-3* • Quadrant Global Pin Name**

I/O Type	Beginning of I/O Name	Notes
Single-Ended	GAAO/IOuxwByVz GAA1/IOuxwByVz GAA2/IOuxwByVz	Only one of the I/Os can be directly connected to a quadrant global at a time
	GABO/IOuxwByVz GAB1/IOuxwByVz GAB2/IOuxwByVz	Only one of the I/Os can be directly connected to a quadrant global at a time.
	GAC0/IOuxwByVz GAC1/IOuxwByVz GAC2/IOuxwByVz	Only one of the I/Os can be directly connected to a quadrant global at a time.
	GBAO/IOuxwByVz GBA1/IOuxwByVz GBA2/IOuxwByVz	Only one of the I/Os can be directly connected to a global at a time.
	GBBO/IOuxwByVz GBB1/IOuxwByVz GBB2/IOuxwByVz	Only one of the I/Os can be directly connected to a global at a time.
	GBC0/IOuxwByVz GBC1/IOuxwByVz GBC2/IOuxwByVz	Only one of the I/Os can be directly connected to a global at a time.
	GDAO/IOuxwByVz GDA1/IOuxwByVz GDA2/IOuxwByVz	Only one of the I/Os can be directly connected to a global at a time.
	GDBO/IOuxwByVz GDB1/IOuxwByVz GDB2/IOuxwByVz	Only one of the I/Os can be directly connected to a global at a time.
	GDC0/IOuxwByVz GDC1/IOuxwByVz GDC2/IOuxwByVz	Only one of the I/Os can be directly connected to a global at a time.
	GEAO/IOuxwByVz GEA1/IOuxwByVz GEA2/IOuxwByVz	Only one of the I/Os can be directly connected to a global at a time.
	GEBO/IOuxwByVz GEB1/IOuxwByVz GEB2/IOuxwByVz	Only one of the I/Os can be directly connected to a global at a time.
	GEC0/IOuxwByVz GEC1/IOuxwByVz GEC2/IOuxwByVz	Only one of the I/Os can be directly connected to a global at a time.

Note: Only one of the I/Os can be directly connected to a quadrant at a time.

List of Changes

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
	Notes were added where appropriate to point out that IGLOO nano and ProASIC3 nano devices do not support differential inputs (SAR 21449).	N/A
	The "Global Architecture" section and "VersaNet Global Network Distribution" section were revised for clarity (SARs 20646, 24779).	47, 49
	The "I/O Banks and Global I/Os" section was moved earlier in the document, renamed to "Chip and Quadrant Global I/Os", and revised for clarity. Figure 3-4 • Global Connections Details, Figure 3-6 • Global Inputs, Table 3-2 • Chip Global Pin Name, and Table 3-3 • Quadrant Global Pin Name are new (SARs 20646, 24779).	51
	The "Clock Aggregation Architecture" section was revised (SARs 20646, 24779).	57
	Figure 3-7 • Chip Global Aggregation was revised (SARs 20646, 24779).	59
	The "Global Macro and Placement Selections" section is new (SARs 20646, 24779).	64
v1.4 (December 2008)	The "Global Architecture" section was updated to include 10 k devices, and to include information about VersaNet global support for IGLOO nano devices.	47
	The Table 3-1 • Flash-Based FPGAs was updated to include IGLOO nano and ProASIC3 nano devices.	48
	The "VersaNet Global Network Distribution" section was updated to include 10 k devices and to note an exception in global lines for nano devices.	49
	Figure 3-2 • Simplified VersaNet Global Network (30 k gates and below) is new.	50
	The "Spine Architecture" section was updated to clarify support for 10 k and nano devices.	57
	Table 3-4 • Globals/Spines/Rows for IGLOO and ProASIC3 Devices was updated to include IGLOO nano and ProASIC3 nano devices.	57
	The figure in the CLKBUF_LVDS/LVPECL row of Table 3-8 • Clock Macros was updated to change CLKBIBUF to CLKBUF.	62
v1.3 (October 2008)	A third bullet was added to the beginning of the "Global Architecture" section: In Fusion devices, the west CCC also contains a PLL core. In the two larger devices (AFS600 and AFS1500), the west and east CCCs each contain a PLL.	47
	The "Global Resource Support in Flash-Based Devices" section was revised to include new families and make the information more concise.	48
	Table 3-4 • Globals/Spines/Rows for IGLOO and ProASIC3 Devices was updated to include A3PE600/L in the device column.	57
	Table note 1 was revised in Table 3-9 • I/O Standards within CLKBUF to include AFS600 and AFS1500.	63
v1.2 (June 2008)	The following changes were made to the family descriptions in Table 3-1 • Flash-Based FPGAs: • ProASIC3L was updated to include 1.5 V. • The number of PLLs for ProASIC3E was changed from five to six.	48

- Use quadrant global region assignments by finding the clock net associated with the CCC macro under the Nets tab and creating a quadrant global region for the net, as shown in Figure 4-33.

Figure 4-33 **• Quadrant Clock Assignment for a Global Net**

External I/O–Driven CCCs

The above-mentioned recommendation for proper layout techniques will ensure the correct assignment. It is possible that, especially with External I/O–Driven CCC macros, placement of the CCC macro in a desired location may not be achieved. For example, assigning an input port of an External I/O–Driven CCC near a particular CCC location does not guarantee global assignments to the desired location. This is because the clock inputs of External I/O–Driven CCCs can be assigned to any I/O location; therefore, it is possible that the CCC connected to the clock input will be routed to a location other than the one closest to the I/O location, depending on resource availability and placement constraints.

Clock Placer

The clock placer is a placement engine for low power flash devices that places global signals on the chip global and quadrant global networks. Based on the clock assignment constraints for the chip global and quadrant global clocks, it will try to satisfy all constraints, as well as creating quadrant clock regions when necessary. If the clock placer fails to create the quadrant clock regions for the global signals, it will report an error and stop Layout.

The user must ensure that the constraints set to promote clock signals to quadrant global networks are valid.

Cascading CCCs

The CCCs in low power flash devices can be cascaded. Cascading CCCs can help achieve more accurate PLL output frequency results than those achievable with a single CCC. In addition, this technique is useful when the user application requires the output clock of the PLL to be a multiple of the reference clock by an integer greater than the maximum feedback divider value of the PLL (divide by 128) to achieve the desired frequency.

For example, the user application may require a 280 MHz output clock using a 2 MHz input reference clock, as shown in Figure 4-34 on page 126.

FlashROM Security

Low power flash devices have an on-chip Advanced Encryption Standard (AES) decryption core, combined with an enhanced version of the Microsemi flash-based lock technology (FlashLock®). Together, they provide unmatched levels of security in a programmable logic device. This security applies to both the FPGA core and FlashROM content. These devices use the 128-bit AES (Rijndael) algorithm to encrypt programming files for secure transmission to the on-chip AES decryption core. The same algorithm is then used to decrypt the programming file. This key size provides approximately 3.4×10^{38} possible 128-bit keys. A computing system that could find a DES key in a second would take approximately 149 trillion years to crack a 128-bit AES key. The 128-bit FlashLock feature in low power flash devices works via a FlashLock security Pass Key mechanism, where the user locks or unlocks the device with a user-defined key. Refer to the "Security in Low Power Flash Devices" section on page 301.

If the device is locked with certain security settings, functions such as device read, write, and erase are disabled. This unique feature helps to protect against invasive and noninvasive attacks. Without the correct Pass Key, access to the FPGA is denied. To gain access to the FPGA, the device first must be unlocked using the correct Pass Key. During programming of the FlashROM or the FPGA core, you can generate the security header programming file, which is used to program the AES key and/or FlashLock Pass Key. The security header programming file can also be generated independently of the FlashROM and FPGA core content. The FlashLock Pass Key is not stored in the FlashROM.

Low power flash devices with AES-based security allow for secure remote field updates over public networks such as the Internet, and ensure that valuable intellectual property (IP) remains out of the hands of IP thieves. Figure 5-5 shows this flow diagram.

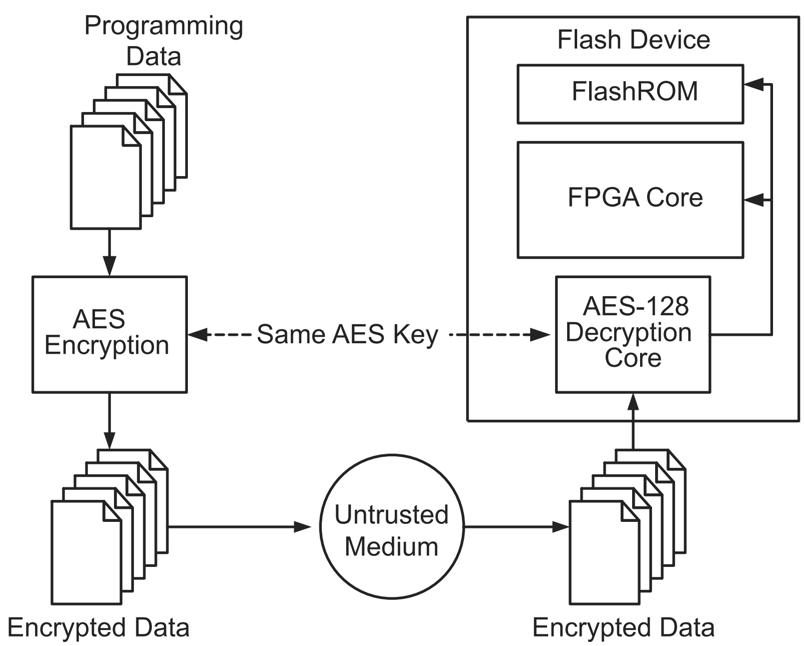


Figure 5-5 **• Programming FlashROM Using AES**

FlashROM Generation and Instantiation in the Design

The SmartGen core generator, available in Libero SoC and Designer, is the only tool that can be used to generate the FlashROM content. SmartGen has several user-friendly features to help generate the FlashROM contents. Instead of selecting each byte and assigning values, you can create a region within a page, modify the region, and assign properties to that region. The FlashROM user interface, shown in Figure 5-10, includes the configuration grid, existing regions list, and properties field. The properties field specifies the region-specific information and defines the data used for that region. You can assign values to the following properties:

1. Static Fixed Data—Enables you to fix the data so it cannot be changed during programming time. This option is useful when you have fixed data stored in this region, which is required for the operation of the design in the FPGA. Key storage is one example.
2. Static Modifiable Data—Select this option when the data in a particular region is expected to be static data (such as a version number, which remains the same for a long duration but could conceivably change in the future). This option enables you to avoid changing the value every time you enter new data.
3. Read from File—This provides the full flexibility of FlashROM usage to the customer. If you have a customized algorithm for generating the FlashROM data, you can specify this setting. You can then generate a text file with data for as many devices as you wish to program, and load that into the FlashPoint programming file generation software to get programming files that include all the data. SmartGen will optionally pass the location of the file where the data is stored if the file is specified in SmartGen. Each text file has only one type of data format (binary, decimal, hex, or ASCII text). The length of each data file must be shorter than or equal to the selected region length. If the data is shorter than the selected region length, the most significant bits will be padded with 0s. For multiple text files for multiple regions, the first lines are for the first device. In SmartGen, **Load Sim. Value From File** allows you to load the first device data in the MEM file for simulation.
4. Auto Increment/Decrement—This scenario is useful when you specify the contents of FlashROM for a large number of devices in a series. You can specify the step value for the serial number and a maximum value for inventory control. During programming file generation, the actual number of devices to be programmed is specified and a start value is fed to the software.

Figure 5-10 **• SmartGen GUI of the FlashROM**

Figure 5-12 shows the programming file generator, which enables different STAPL file generation methods. When you select **Program FlashROM** and choose the UFC file, the FlashROM Settings window appears, as shown in Figure 5-13. In this window, you can select the FlashROM page you want to program and the data value for the configured regions. This enables you to use a different page for different programming files.

Figure 5-12 **• Programming File Generator**

Figure 5-13 **• Setting FlashROM during Programming File Generation**

The programming hardware and software can load the FlashROM with the appropriate STAPL file. Programming software handles the single STAPL file that contains multiple FlashROM contents for multiple devices, and programs the FlashROM in sequential order (e.g., for device serialization). This feature is supported in the programming software. After programming with the STAPL file, you can run DEVICE_INFO to check the FlashROM content.

Example: For a bus consisting of 20 equidistant loads, the terminations given in EQ 1 provide the required differential voltage, in worst-case industrial operating conditions, at the farthest receiver:

$R_S = 60\ \Omega$, $R_T = 70\ \Omega$, given $Z_O = 50\ \Omega$ (2") and $Z_{stub} = 50\ \Omega$ (~1.5").

EQ 1

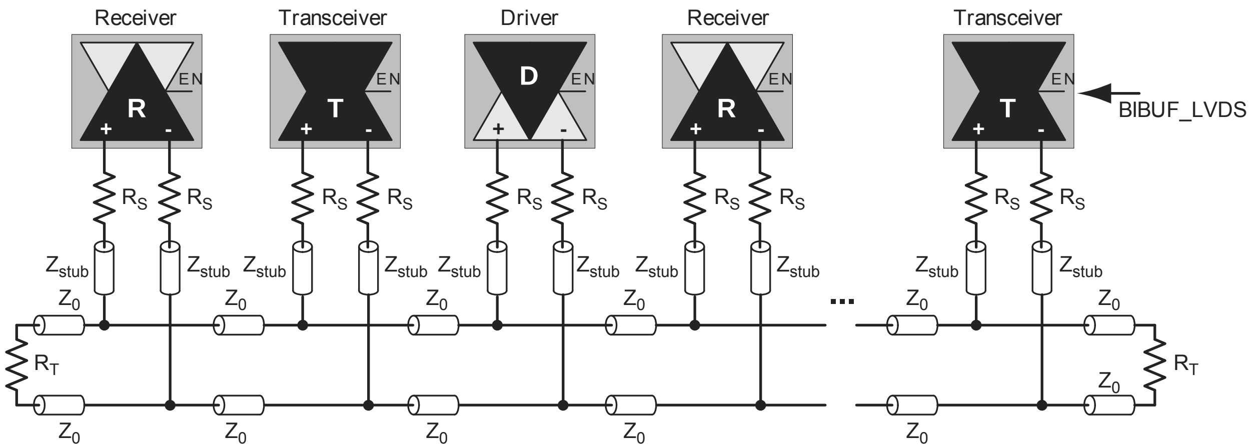


Figure 7-8 **• A B-LVDS/M-LVDS Multipoint Application Using LVDS I/O Buffers**

IGLOO and ProASIC3

For boards and cards with three levels of staging, card power supplies must have time to reach their final values before the I/Os are connected. Pay attention to the sizing of power supply decoupling capacitors on the card to ensure that the power supplies are not overloaded with capacitance.

Cards with three levels of staging should have the following sequence:

- Grounds
- Powers
- I/Os and other pins

For Level 3 and Level 4 compliance with the 30K gate device, cards with two levels of staging should have the following sequence:

- Grounds
- Powers, I/Os, and other pins

Cold-Sparing Support

Cold-sparing refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

The resistor value is calculated based on the decoupling capacitance on a given power supply. The RC constant should be greater than 3 µs.

To remove resistor current during operation, it is suggested that the resistor be disconnected (e.g., with an NMOS switch) from the power supply after the supply has reached its final value. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 373 for details on cold-sparing.

Cold-sparing means that a subsystem with no power applied (usually a circuit board) is electrically connected to the system that is in operation. This means that all input buffers of the subsystem must present very high input impedance with no power applied so as not to disturb the operating portion of the system.

The 30 k gate devices fully support cold-sparing, since the I/O clamp diode is always off (see Table 7-12 on page 193). If the 30 k gate device is used in applications requiring cold-sparing, a discharge path from the power supply to ground should be provided. This can be done with a discharge resistor or a switched resistor. This is necessary because the 30K gate devices do not have built-in I/O clamp diodes.

For other IGLOO and ProASIC3 devices, since the I/O clamp diode is always active, cold-sparing can be accomplished either by employing a bus switch to isolate the device I/Os from the rest of the system or by driving each I/O pin to 0 V. If the resistor is chosen, the resistor value must be calculated based on decoupling capacitance on a given power supply on the board (this decoupling capacitance is in parallel with the resistor). The RC time constant should ensure full discharge of supplies before cold-sparing functionality is required. The resistor is necessary to ensure that the power pins are discharged to ground every time there is an interruption of power to the device.

IGLOOe and ProASIC3E devices support cold-sparing for all I/O configurations. Standards, such as PCI, that require I/O clamp diodes can also achieve cold-sparing compliance, since clamp diodes get disconnected internally when the supplies are at 0 V.

When targeting low power applications, I/O cold-sparing may add additional current if a pin is configured with either a pull-up or pull-down resistor and driven in the opposite direction. A small static current is induced on each I/O pin when the pin is driven to a voltage opposite to the weak pull resistor. The current is equal to the voltage drop across the input pin divided by the pull resistor. Refer to the "Detailed I/O DC Characteristics" section of the appropriate family datasheet for the specific pull resistor value for the corresponding I/O standard.

For example, assuming an LVTTL 3.3 V input pin is configured with a weak pull-up resistor, a current will flow through the pull-up resistor if the input pin is driven LOW. For LVTTL 3.3 V, the pull-up resistor is ~45 kΩ, and the resulting current is equal to 3.3 V / 45 kΩ = 73 µA for the I/O pin. This is true also when a weak pull-down is chosen and the input pin is driven HIGH. This current can be avoided by driving the input LOW when a weak pull-down resistor is used and driving it HIGH when a weak pull-up resistor is used.

This current draw can occur in the following cases:

Simultaneously Switching Outputs (SSOs) and Printed Circuit Board Layout

Each I/O voltage bank has a separate ground and power plane for input and output circuits (VMV/GNDQ for input buffers and VCCI/GND for output buffers). This isolation is necessary to minimize simultaneous switching noise from the input and output (SSI and SSO). The switching noise (ground bounce and power bounce) is generated by the output buffers and transferred into input buffer circuits, and vice versa.

Since voltage bounce originates on the package inductance, the VMV and VCCI supplies have separate package pin assignments. For the same reason, GND and GNDQ also have separate pin assignments.

The VMV and VCCI pins must be shorted to each other on the board. Also, the GND and GNDQ pins must be shorted to each other on the board. This will prevent unwanted current draw from the power supply.

SSOs can cause signal integrity problems on adjacent signals that are not part of the SSO bus. Both inductive and capacitive coupling parasitics of bond wires inside packages and of traces on PCBs will transfer noise from SSO busses onto signals adjacent to those busses. Additionally, SSOs can produce ground bounce noise and VCCI dip noise. These two noise types are caused by rapidly changing currents through GND and VCCI package pin inductances during switching activities (EQ 2 and EQ 3).

$$\text{Ground bounce noise voltage} = L(GND) \times di/dt$$

EQ 2

$$\text{VCCI dip noise voltage} = L(VCCI) \times di/dt$$

EQ 3

Any group of four or more input pins switching on the same clock edge is considered an SSO bus. The shielding should be done both on the board and inside the package unless otherwise described.

In-package shielding can be achieved in several ways; the required shielding will vary depending on whether pins next to the SSO bus are LVTTL/LVCMOS inputs, LVTTL/LVCMOS outputs, or GTL/SSTL/HSTL/LVDS/LVPECL inputs and outputs. Board traces in the vicinity of the SSO bus have to be adequately shielded from mutual coupling and inductive noise that can be generated by the SSO bus. Also, noise generated by the SSO bus needs to be reduced inside the package.

PCBs perform an important function in feeding stable supply voltages to the IC and, at the same time, maintaining signal integrity between devices.

Key issues that need to be considered are as follows:

- Power and ground plane design and decoupling network design
- Transmission line reflections and terminations

For extensive data per package on the SSO and PCB issues, refer to the "ProASIC3/E SSO and Pin Placement and Guidelines" chapter of the *ProASIC3 FPGA Fabric User’s Guide*.

List of Changes

The following table lists critical changes that were made in each revision of the document.

Date	Changes	Page
August 2012	Figure 8-1 • DDR Configured I/O Block Logical Representation and Figure 8-3 • DDR Configured I/O Block Logical Representation were revised to indicate that resets on registers 1, 3, 4, and 5 are active high rather than active low. The title of the figures was revised from "I/O Block Logical Representation" (SAR 40685).	213, 220
	AGLE1500 was removed from Table 8-2 • Supported I/O Standards because it is not a valid offering. LVCMOS 1.2 was added to the single-ended standards. LVCMOS 1.2 was added to Table 8-3 • VCCI Voltages and Compatible IGLOOe and ProASIC3E Standards (SAR 33207).	215, 217
	Lack of a heading for the "User I/O Naming Convention" section made the information difficult to locate. A heading now introduces the user I/O naming conventions (SAR 38059).	245
	Figure 8-5 • Simplified I/O Buffer Circuitry and Table 8-8 • Programmable I/O Features (user control via I/O Attribute Editor) were modified to indicate that programmable input delay control is applicable only to ProASIC3E, IGLOOe, ProASIC3EL, and RT ProASIC3 devices (SAR 39666).	222, 227
	The hyperlink for the *Board-Level Considerations* application note was corrected (SAR 36663).	246, 248
June 2011	Figure 8-1 • DDR Configured I/O Block Logical Representation and Figure 8-3 • DDR Configured I/O Block Logical Representation were revised so that the I/O_CLR and I/O_OCLK nets are no longer joined in front of Input Register 3 but instead on the branch of the CLR/PRE signal (SAR 26052).	213, 220
	The "Pro I/Os—IGLOOe, ProASIC3EL, and ProASIC3E" section was revised. Formerly it stated, "3.3 V PCI and 3.3 V PCI-X are 5 V–tolerant." This sentence now reads, "3.3 V PCI and 3.3 V PCI-X can be configured to be 5 V–tolerant" (SAR 20983).	215
	Table 8-5 • Legal IGLOOe and ProASIC3E I/O Usage Matrix within the Same Bank was revised as follows (SAR 22467): The combination of 3.3 V I/O bank voltage with 1.50 V minibank voltage and LVDS, B-LVDS, M-LVDS, and DDR was made an illegal combination (now gray instead of white). The combination of 2.5 V I/O bank voltage with no minibank voltage and LVDS, B-LVDS, M-LVDS, and DDR was made a valid combination (now white instead of gray).	217
	The following sentence was removed from the "LVCMOS (Low-Voltage CMOS)" section (SAR 22634): "All these versions use a 3.3 V–tolerant CMOS input buffer and a push-pull output buffer."	223
	The "Electrostatic Discharge Protection" section was revised to remove references to tolerances (refer to the *Reliability Report* for tolerances). The Machine Model (MM) is not supported and was deleted from this section (SAR 24385).	231
	The "I/O Interfacing" section was revised to state that low power flash devices are 5 V–input– and 5 V–output–tolerant if certain I/O standards are selected, removing "without adding any extra circuitry," which was incorrect (SAR 21404).	247
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
v1.4 (December 2008)	The terminology in the "Low Power Flash Device I/O Support" section was revised.	214

4. Right-click and then choose **Highlight VREF range**. All the pins covered by that VREF pin will be highlighted (Figure 9-14).

Figure 9-14 **• VREF Range**

Using PinEditor or ChipPlanner, VREF pins can also be assigned (Figure 9-15).

Figure 9-15 **• Assigning VREF from PinEditor**

To unassign a VREF pin:

1. Select the pin to unassign.
2. Right-click and choose **Use Pin for VREF.** The check mark next to the command disappears. The VREF pin is now a regular pin.

Resetting the pin may result in unassigning I/O cores, even if they are locked. In this case, a warning message appears so you can cancel the operation.

After you assign the VREF pins, right-click a VREF pin and choose **Highlight VREF Range** to see how many I/Os are covered by that pin. To unhighlight the range, choose **Unhighlight All** from the **Edit** menu.

List of Changes

The following table lists critical changes that were made in each revision of the document.

Date	Changes	Page
August 2012	The notes in Table 9-2 • Designer State (resulting from I/O attribute modification) were revised to clarify which device families support programmable input delay (SAR 39666).	253
June 2011	Figure 9-2 • SmartGen Catalog was updated (SAR 24310). Figure 8-3 • Expanded I/O Section and the step associated with it were deleted to reflect changes in the software.	254
	The following rule was added to the "VREF Rules for the Implementation of Voltage-Referenced I/O Standards" section: Only minibanks that contain input or bidirectional I/Os require a VREF. A VREF is not needed for minibanks composed of output or tristated I/Os (SAR 24310).	265
July 2010	Notes were added where appropriate to point out that IGLOO nano and ProASIC3 nano devices do not support differential inputs (SAR 21449).	N/A
v1.4 (December 2008)	IGLOO nano and ProASIC3 nano devices were added to Table 9-1 • Flash-Based FPGAs.	252
	The notes for Table 9-2 • Designer State (resulting from I/O attribute modification) were revised to indicate that skew control and input delay do not apply to nano devices.	253
v1.3 (October 2008)	The "Flash FPGAs I/O Support" section was revised to include new families and make the information more concise.	252
v1.2 (June 2008)	The following changes were made to the family descriptions in Table 9-1 • Flash-Based FPGAs: • ProASIC3L was updated to include 1.5 V. • The number of PLLs for ProASIC3E was changed from five to six.	252
v1.1 (March 2008)	This document was previously part of the *I/O Structures in IGLOO and ProASIC3 Devices* document. The content was separated and made into a new document.	N/A
	Table 9-2 • Designer State (resulting from I/O attribute modification) was updated to include note 2 for IGLOO PLUS.	253

I/O Cell Architecture

Low power flash devices support DDR in the I/O cells in four different modes: Input, Output, Tristate, and Bidirectional pins. For each mode, different I/O standards are supported, with most I/O standards having special sub-options. For the ProASIC3 nano and IGLOO nano devices, DDR is supported only in the 60 k, 125 k, and 250 k logic densities. Refer to Table 10-2 for a sample of the available I/O options. Additional I/O options can be found in the relevant family datasheet.

***Table 10-2* • DDR I/O Options**

DDR Register Type	I/O Type	I/O Standard	Sub-Options	Comments
Receive Register	Input	Normal	None	3.3 V TTL (default)
		LVCMOS	Voltage	1.5 V, 1.8 V, 2.5 V, 5 V (1.5 V default)
			Pull-Up	None (default)
		PCI/PCI-X	None	
		GTL/GTL+	Voltage	2.5 V, 3.3 V (3.3 V default)
		HSTL	Class	I / II (I default)
		SSTL2/SSTL3	Class	I / II (I default)
		LVPECL	None	
		LVDS	None	
Transmit Register	Output	Normal	None	3.3 V TTL (default)
		LVTTL	Output Drive	2, 4, 6, 8, 12, 16, 24, 36 mA (8 mA default)
			Slew Rate	Low/high (high default)
		LVCMOS	Voltage	1.5 V, 1.8 V, 2.5 V, 5 V (1.5 V default)
		PCI/PCI-X	None	
		GTL/GTL+	Voltage	1.8 V, 2.5 V, 3.3 V (3.3 V default)
		HSTL	Class	I / II (I default)
		SSTL2/SSTL3	Class	I / II (I default)
		LVPECL*	None	
		LVDS*	None	

*Note: *IGLOO nano and ProASIC3 nano devices do not support differential inputs.*

Microsemi

11 – Programming Flash Devices

Introduction

This document provides an overview of the various programming options available for the Microsemi flash families. The electronic version of this document includes active links to all programming resources, which are available at http://www.microsemi.com/soc/products/hardware/default.aspx. For Microsemi antifuse devices, refer to the *Programming Antifuse Devices* document.

Summary of Programming Support

FlashPro4 and FlashPro3 are high-performance in-system programming (ISP) tools targeted at the latest generation of low power flash devices offered by the SmartFusion,® Fusion, IGLOO,® and ProASIC®3 families, including ARM-enabled devices. FlashPro4 and FlashPro3 offer extremely high performance through the use of USB 2.0, are high-speed compliant for full use of the 480 Mbps bandwidth, and can program ProASIC3 devices in under 30 seconds. Powered exclusively via USB, FlashPro4 and FlashPro3 provide a VPUMP voltage of 3.3 V for programming these devices.

FlashPro4 replaced FlashPro3 in 2010. FlashPro4 supports SmartFusion, Fusion, ProASIC3,and IGLOO devices as well as future generation flash devices. FlashPro4 also adds 1.2 V programming for IGLOO nano V2 devices. FlashPro4 is compatible with FlashPro3; however it adds a programming mode (PROG_MODE) signal to the previously unused pin 4 of the JTAG connector. The PROG_MODE goes high during programming and can be used to turn on a 1.5 V external supply for those devices that require 1.5 V for programming. If both FlashPro3 and FlashPro4 programmers are used for programming the same boards, pin 4 of the JTAG connector must not be connected to anything on the board because FlashPro4 uses pin 4 for PROG_MODE.

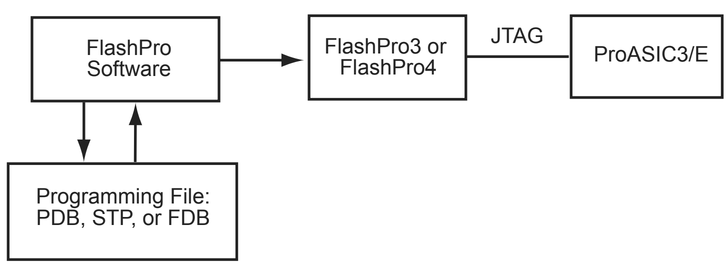


Figure 11-1 **• FlashPro Programming Setup**

2. Choose the appropriate security level setting and enter a FlashLock Pass Key. The default is the **Medium** security level (Figure 12-12). Click **Next**.

   If you want to select different options for the FPGA and/or FlashROM, this can be set by clicking **Custom Level**. Refer to the "Advanced Options" section on page 322 for different custom security level options and descriptions of each.

Figure 12-12 **• Medium Security Level Selected for Low Power Flash Devices**

Programming File Header Definition

In each STAPL programming file generated, there will be information about how the AES key and FlashLock Pass Key are configured. Table 12-8 shows the header definitions in STAPL programming files for different security levels.

***Table 12-8* • STAPL Programming File Header Definitions by Security Level**

Security Level	STAPL File Header Definition
No security (no FlashLock Pass Key or AES key)	`NOTE "SECURITY" "Disable";`
FlashLock Pass Key with no AES key	`NOTE "SECURITY" "KEYED ";`
FlashLock Pass Key with AES key	`NOTE "SECURITY" "KEYED ENCRYPT ";`
Permanent Security Settings option enabled	`NOTE "SECURITY" "PERMLOCK ENCRYPT ";`
AES-encrypted FPGA array (for programming updates)	`NOTE "SECURITY" "ENCRYPT CORE ";`
AES-encrypted FlashROM (for programming updates)	`NOTE "SECURITY" "ENCRYPT FROM ";`
AES-encrypted FPGA array and FlashROM (for programming updates)	`NOTE "SECURITY" "ENCRYPT FROM CORE ";`

Example File Headers

STAPL Files Generated with FlashLock Key and AES Key Containing Key Information

- FlashLock Key / AES key indicated in STAPL file header definition
- Intended ONLY for secured/trusted environment programming applications

```
=============================================
NOTE "CREATOR" "Designer Version: 6.1.1.108";
NOTE "DEVICE" "A3PE600";
NOTE "PACKAGE" "208 PQFP";
NOTE "DATE" "2005/04/08";
NOTE "STAPL_VERSION" "JESD71";
NOTE "IDCODE" "$123261CF";
NOTE "DESIGN" "counter32";
NOTE "CHECKSUM" "$EDB9";
NOTE "SAVE_DATA" "FRomStream";
NOTE "SECURITY" "KEYED ENCRYPT ";
NOTE "ALG_VERSION" "1";
NOTE "MAX_FREQ" "20000000";
NOTE "SILSIG" "$00000000";
NOTE "PASS_KEY" "$00123456789012345678901234567890";
NOTE "AES_KEY" "$ABCDEFABCDEFABCDEFABCDEFABCDEFAB";
==============================================
```

17 – UJTAG Applications in Microsemi's Low Power Flash Devices

Introduction

In Fusion, IGLOO, and ProASIC3 devices, there is bidirectional access from the JTAG port to the core VersaTiles during normal operation of the device (Figure 17-1). User JTAG (UJTAG) is the ability for the design to use the JTAG ports for access to the device for updates, etc. While regular JTAG is used, the UJTAG tiles, located at the southeast area of the die, are directly connected to the JTAG Test Access Port (TAP) Controller in normal operating mode. As a result, all the functional blocks of the device, such as Clock Conditioning Circuits (CCCs) with PLLs, SRAM blocks, embedded FlashROM, flash memory blocks, and I/O tiles, can be reached via the JTAG ports. The UJTAG functionality is available by instantiating the UJTAG macro directly in the source code of a design. Access to the FPGA core VersaTiles from the JTAG ports enables users to implement different applications using the TAP Controller (JTAG port). This document introduces the UJTAG tile functionality and discusses a few application examples. However, the possible applications are not limited to what is presented in this document. UJTAG can serve different purposes in many designs as an elementary or auxiliary part of the design. For detailed usage information, refer to the "Boundary Scan in Low Power Flash Devices" section on page 357.

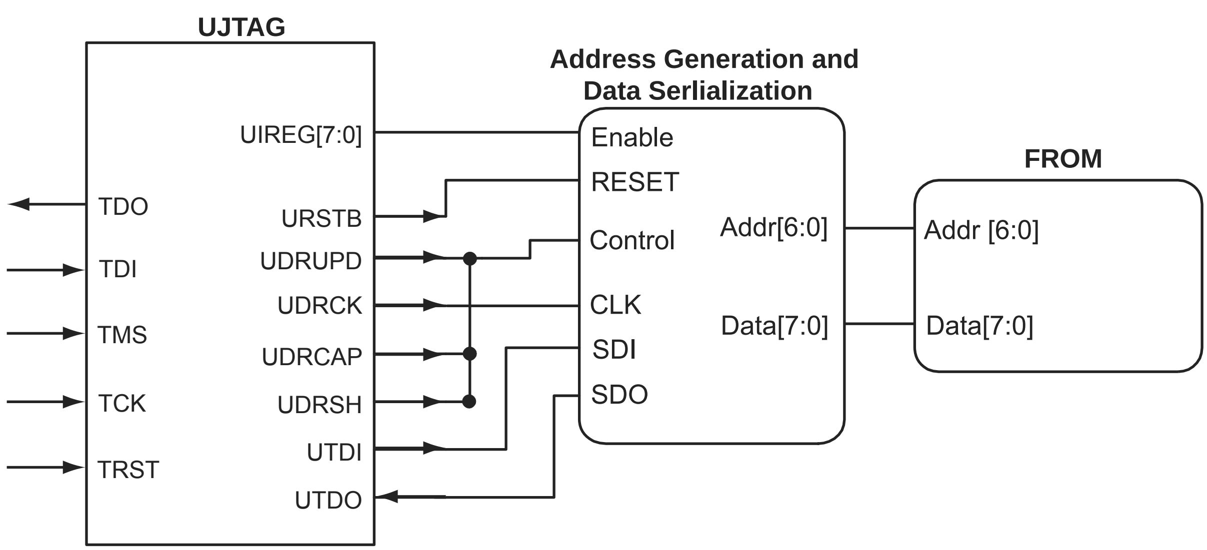


Figure 17-1 • **Block Diagram of Using UJTAG to Read FlashROM Contents**

Flash Devices Support Power-Up Behavior

The flash FPGAs listed in Table 18-1 support power-up behavior and the functions described in this document.

***Table 18-1* • Flash-Based FPGAs**

Series	Family*	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications

*Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.*

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 18-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 18-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.